

# Jörn M Hvam

## List of Publications by Year in descending order

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265  
papers

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31976

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times ranked

5301  
citing authors

#	ARTICLE	IF	CITATIONS
1	Build up of off-diagonal long-range order in microcavity exciton-polaritons across the parametric threshold. <i>Optics Express</i> , 2013, 21, 10792.	3.4	8
2	Polarized emission in polariton condensates: Switching in a one-dimensional natural trap versus inversion in two dimensions. <i>Physical Review B</i> , 2013, 88, .	3.2	5
3	Polarization insensitive wavelength conversion in a dispersion-engineered silicon waveguide. <i>Optics Express</i> , 2012, 20, 16374.	3.4	25
4	Self-phase modulation of a single-cycle terahertz pulse by nonlinear free-carrier response in a semiconductor. <i>Physical Review B</i> , 2012, 85, .	3.2	79
5	Coherence properties of exciton polariton OPO condensates in one and two dimensions. <i>New Journal of Physics</i> , 2012, 14, 075018.	2.9	19
6	Spontaneous emission from large quantum dots in nanostructures: Exciton-photon interaction beyond the dipole approximation. <i>Physical Review B</i> , 2012, 86, .	3.2	50
7	Silicon Photonics for Signal Processing of Tbit/s Serial Data Signals. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2012, 18, 996-1005.	2.9	43
8	Optical Waveform Sampling and Error-Free Demultiplexing of 1.28 Tb/s Serial Data in a Nanoengineered Silicon Waveguide. <i>Journal of Lightwave Technology</i> , 2011, 29, 426-431.	4.6	66
9	Silicon-on-insulator polarization splitting and rotating device for polarization diversity circuits. <i>Optics Express</i> , 2011, 19, 12646.	3.4	159
10	Ultra-high-speed wavelength conversion in a silicon photonic chip. <i>Optics Express</i> , 2011, 19, 19886.	3.4	72
11	One-to-six WDM multicasting of DPSK signals based on dual-pump four-wave mixing in a silicon waveguide. <i>Optics Express</i> , 2011, 19, 24448.	3.4	40
12	Ultra-high-speed optical serial-to-parallel data conversion by time-domain optical Fourier transformation in a silicon nanowire. <i>Optics Express</i> , 2011, 19, B825.	3.4	44
13	Efficient and compact TEâ€™TM polarization converter built on silicon-on-insulator platform with a simple fabrication process. <i>Optics Letters</i> , 2011, 36, 1059.	3.3	98
14	Quantumâ€•excitons in nanostructured environments. <i>Physica Status Solidi (B): Basic Research</i> , 2011, 248, 375-383.	1.5	2
15	On the interpretation of wave function overlaps in quantum dots. <i>Physica Status Solidi (B): Basic Research</i> , 2011, 248, 855-858.	1.5	4
16	15-THz Tunable Wavelength Conversion of Picosecond Pulses in a Silicon Waveguide. <i>IEEE Photonics Technology Letters</i> , 2011, 23, 1409-1411.	2.5	19
17	Probing long-lived dark excitons in self-assembled quantum dots. <i>Physical Review B</i> , 2010, 81, .	3.2	67
18	Toward superlensing with metalâ€™dielectric composites and multilayers. <i>Applied Physics B: Lasers and Optics</i> , 2010, 100, 93-100.	2.2	37

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19	Ultra-low-loss inverted taper coupler for silicon-on-insulator ridge waveguide. Optics Communications, 2010, 283, 3678-3682.	2.1	261
20	High-efficiency, large-bandwidth silicon-on-insulator grating coupler based on a fully-etched photonic crystal structure. Applied Physics Letters, 2010, 96, .	3.3	96
21	Lambda shifted photonic crystal cavity laser. Applied Physics Letters, 2010, 97, 191109.	3.3	3
22	Thermoplastic microcantilevers fabricated by nanoimprint lithography. Journal of Micromechanics and Microengineering, 2010, 20, 015009.	2.6	12
23	Large quantum dots with small oscillator strength. Physical Review B, 2010, 82, .	3.2	27
24	Optimization of VCSELs for Self-Mixing Sensing. IEEE Photonics Technology Letters, 2010, 22, 667-669.	2.5	9
25	Tunable Microwave Phase Shifter Based on Silicon-on-Insulator Microring Resonator. IEEE Photonics Technology Letters, 2010, 22, 869-871.	2.5	59
26	1.28-Tb/s Demultiplexing of an OTDM DPSK Data Signal Using a Silicon Waveguide. IEEE Photonics Technology Letters, 2010, 22, 1762-1764.	2.5	53
27	Widely tunable microwave phase shifter based on silicon-on-insulator dual-microring resonator. Optics Express, 2010, 18, 6172.	3.4	76
28	Measuring the dynamics of second-order photon correlation functions inside a pulse with picosecond time resolution. Optics Express, 2010, 18, 20229.	3.4	38
29	Design of one-dimensional optical pulse-shaping filters by time-domain topology optimization. Applied Physics Letters, 2009, 95, .	3.3	23
30	Frequency dependence of the radiative decay rate of excitons in self-assembled quantum dots: Experiment and theory. Physical Review B, 2009, 80, .	3.2	56
31	Self-mixing interferometry in vertical-cavity surface-emitting lasers for nanomechanical cantilever sensing. Applied Physics Letters, 2009, 94, .	3.3	22
32	Higher-Order Photon Bunching in a Semiconductor Microcavity. Science, 2009, 325, 297-300.	12.6	106
33	Size dependence of the wavefunction of self-assembled InAs quantum dots from time-resolved optical measurements. Physical Review B, 2008, 77, .	3.2	119
34	Long luminescence lifetime in self-assembled InGaAs/GaAs quantum dots at room temperature. Applied Physics Letters, 2008, 93, .	3.3	5
35	Short exciton radiative lifetime in submonolayer InGaAs/GaAs quantum dots. Applied Physics Letters, 2008, 92, 063103.	3.3	7
36	Low-noise monolithic mode-locked semiconductor lasers through low-dimensional structures. Proceedings of SPIE, 2008, , .	0.8	6

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37	Influence of <i>in situ</i> annealing on carrier dynamics in InGaAs/GaAs quantum dots. Nanotechnology, 2007, 18, 325401.	2.6	4
38	Long All-Active Monolithic Mode-Locked Lasers With Surface-Etched Bragg Gratings. IEEE Photonics Technology Letters, 2007, 19, 1723-1725.	2.5	9
39	Ultrafast dynamics of quantum-dot semiconductor optical amplifiers. Journal of Materials Science: Materials in Electronics, 2007, 18, 51-55.	2.2	3
40	Carrier dynamics in submonolayer InGaAs $\cdot$ GaAs quantum dots. Applied Physics Letters, 2006, 89, 013113.	3.3	19
41	Dynamic Spatiotemporal Speed Control of Ultrashort Pulses in Quantum-Dot SOAs. IEEE Journal of Quantum Electronics, 2006, 42, 1047-1054.	1.9	19
42	Micromanipulation of organic nanofibers for blue light emitting microstructures. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 1459-1463.	1.8	8
43	Coherent spin dynamics of an interwell excitonic gas in GaAs $\cdot$ AlGaAs coupled quantum wells. Physical Review B, 2006, 73, .	3.2	8
44	Phonon-Induced Polariton Superlattices. Physical Review Letters, 2006, 97, 045501.	7.8	68
45	Collective behavior of a spin-aligned gas of interwell excitons in double quantum wells. JETP Letters, 2005, 81, 108-111.	1.4	2
46	Design and evaluation of mode-locked semiconductor lasers for low noise and high stability (Invited) Tj ETQq0 0 0 rgBT /Overlock 10 Tf		
47	Ultrafast gain dynamics in quantum-dot amplifiers: theoretical analysis and experimental investigations. IEEE Journal of Quantum Electronics, 2005, 41, 1115-1123.	1.9	63
48	Stokes and anti-Stokes photoluminescence towards five different In <sub>x</sub> (Al <sub>0.17</sub> Ga <sub>0.83</sub> ) <sub>1-x</sub> As $\cdot$ Al <sub>0.17</sub> Ga <sub>0.83</sub> As quantum wells. Journal of Applied Physics, 2005, 98, 083527.	2.5	6
49	Propagation of long-range surface plasmon polaritons in photonic crystals. Journal of the Optical Society of America B: Optical Physics, 2005, 22, 2027.	2.1	14
50	Controllable delay of ultrashort pulses in a quantum dot optical amplifier. Optics Express, 2005, 13, 8032.	3.4	63
51	Wide-band residual phase-noise measurements on 40-GHz monolithic mode-locked lasers. IEEE Photonics Technology Letters, 2005, 17, 2388-2390.	2.5	2
52	Submonolayer InGaAs $\cdot$ GaAs quantum-dot lasers with high modal gain and zero-linewidth enhancement factor. Applied Physics Letters, 2004, 85, 3259-3261.	3.3	51
53	Wave-function reconstruction in a graded semiconductor superlattice. Applied Physics A: Materials Science and Processing, 2004, 78, 441-445.	2.3	2
54	Dynamic Dipole $\cdot$ Dipole Interactions Between Excitons in Quantum Dots of Different Sizes. IEEE Nanotechnology Magazine, 2004, 3, 318-327.	2.0	13

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55	Low-Jitter and High-Power 40-GHz All-Active Mode-Locked Lasers. IEEE Photonics Technology Letters, 2004, 16, 975-977.	2.5	63
56	Gain dynamics and saturation in semiconductor quantum dot amplifiers. New Journal of Physics, 2004, 6, 178-178.	2.9	44
57	High-performance 10-...GHz all-active monolithic modelocked semiconductor lasers. Electronics Letters, 2004, 40, 735.	1.0	29
58	Effect of annealing on the structure and optical properties of InGaAs/GaAs quantum dots. Journal of Crystal Growth, 2003, 251, 177-180.	1.5	3
59	Homogeneous linewidth of self-assembled III-V quantum dots observed in single-dot photoluminescence. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 17, 1-6.	2.7	19
60	InGaAs/GaAs quantum-dot quantum-well heterostructure formed by submonolayer deposition. Nanotechnology, 2003, 14, 1259-1261.	2.6	23
61	Dynamics of unidirectional phonon-assisted transport of photoexcited carriers in step-graded In <sub>x</sub> (Al <sub>0.17</sub> Ga <sub>0.83</sub> ) <sub>1-x</sub> As/Al <sub>0.17</sub> Ga <sub>0.83</sub> As multiple quantum wells. Physical Review B, 2003, 67, .	3.2	13
62	Structure and optical anisotropy of vertically correlated submonolayer InAs/GaAs quantum dots. Applied Physics Letters, 2003, 82, 3859-3861.	3.3	62
63	Biexcitons in semiconductor microcavities. Semiconductor Science and Technology, 2003, 18, S351-S360.	2.0	14
64	Semiconductor quantum-dot lasers and amplifiers. , 2002, , .		2
65	Dephasing in Self-organized InAlGaAs Quantum Dots. Physica Scripta, 2002, T101, 143.	2.5	2
66	<title>Coherent interpolariton scattering on moving gratings in microcavity with 25 nm GaAs/AlGaAs single quantum well</title>. , 2002, , .		0
67	Heterodyne technique for measuring the amplitude and phase transfer functions of an optical modulator. IEEE Photonics Technology Letters, 2002, 14, 621-623.	2.5	26
68	Elastic Scattering Dynamics of Cavity Polaritons: Evidence for Time-Energy Uncertainty and Polariton Localization. Physical Review Letters, 2002, 88, 047401.	7.8	65
69	Biexciton Binding Energy in ZnSe Quantum Wells and Quantum Wires. Physica Status Solidi (B): Basic Research, 2002, 231, 11-18.	1.5	11
70	Biexcitonic Bound and Continuum States of Homogeneously and Inhomogeneously Broadened Exciton Resonances. Physica Status Solidi A, 2002, 190, 167-174.	1.7	12
71	Directional Scattering Dynamics of Microcavity Polaritons. Physica Status Solidi A, 2002, 190, 327-332.	1.7	2
72	Coherent Dynamics of Biexcitons in a Semiconductor Microcavity. Physica Status Solidi A, 2002, 190, 383-387.	1.7	2

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73	Long coherence times in self-assembled semiconductor quantum dots. Superlattices and Microstructures, 2002, 31, 97-105.	3.1	8
74	Directional phonon-assisted cascading of photoexcited carriers in stepped $\text{In}_x(\text{Al}_{0.17}\text{Ga}_{0.83})_{1-x}\text{As}/\text{Al}_{0.17}\text{Ga}_{0.83}\text{As}$ multiple quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 182-185.	2.7	5
75	Collective state of interwell excitons in GaAs/AlGaAs double quantum wells under pulse resonance excitation. JETP Letters, 2002, 75, 200-204.	1.4	20
76	Phase diagram of the Bose condensation of interwell excitons in GaAs/AlGaAs double quantum wells. JETP Letters, 2002, 76, 450-455.	1.4	31
77	Long Lived Coherence in Self-Assembled Quantum Dots. Physical Review Letters, 2001, 87, 227401.	7.8	211
78	Spectral signatures of $\hat{\Gamma}^{\pm}(5)$ processes in four-wave mixing of homogeneously broadened excitons. Journal of the Optical Society of America B: Optical Physics, 2001, 18, 1318.	2.1	44
79	Structural and electrooptical characteristics of quantum dots emitting at $1.3 \mu\text{m}$ on gallium arsenide. IEEE Journal of Quantum Electronics, 2001, 37, 1050-1058.	1.9	31
80	Waveguiding in Surface Plasmon Polariton Band Gap Structures. Physical Review Letters, 2001, 86, 3008-3011.	7.8	455
81	Coherent versus incoherent dynamics in InAs quantum-dot active wave guides. Journal of Applied Physics, 2001, 89, 6542-6544.	2.5	3
82	Second-harmonic scanning optical microscopy of semiconductor quantum dots. Optics Communications, 2001, 189, 305-311.	2.1	11
83	Localized excitons in quantum wells show spin relaxation without coherence loss. Physica E: Low-Dimensional Systems and Nanostructures, 2001, 10, 40-44.	2.7	12
84	Spectral Hole-Burning and Carrier-Heating Dynamics in Quantum-Dot Amplifiers: Comparison with Bulk Amplifiers. Physica Status Solidi (B): Basic Research, 2001, 224, 419-423.	1.5	29
85	Excited State Dynamics in $\text{In}_{0.5}\text{Al}_{0.04}\text{Ga}_{0.46}\text{As}/\text{Al}_{0.08}\text{Ga}_{0.92}\text{As}$ Self-Assembled Quantum Dots. Physica Status Solidi (B): Basic Research, 2001, 224, 447-451.	1.5	1
86	Enhanced confinement energy in strained asymmetric T-shaped quantum wires. Journal of Crystal Growth, 2001, 227-228, 966-969.	1.5	7
87	Persistent photoeffects in p-i-n GaAs/AlGaAs heterostructures with double quantum wells. Semiconductors, 2001, 35, 99-105.	0.5	0
88	Ultrashort pulse-propagation effects in a semiconductor optical amplifier: microscopic theory and experiment. IEEE Journal of Selected Topics in Quantum Electronics, 2001, 7, 694-702.	2.9	7
89	Stimulated Secondary Emission from Semiconductor Microcavities. Physical Review Letters, 2001, 86, 5791-5794.	7.8	52
90	Seeding of Polariton Stimulation in a Homogeneously Broadened Microcavity. Physica Status Solidi (B): Basic Research, 2000, 221, 115-120.	1.5	8

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91	Temperature Dependence of the Polariton Linewidth in a GaAs Quantum Well Microcavity. <i>Physica Status Solidi (B): Basic Research</i> , 2000, 221, 143-146.	1.5	1
92	Spin Relaxation without Coherence Loss: Fine-Structure Splitting of Localized Excitons. <i>Physica Status Solidi (B): Basic Research</i> , 2000, 221, 349-353.	1.5	15
93	Linewidth Statistics of Single InGaAs Quantum Dot Photoluminescence Lines. <i>Physica Status Solidi (B): Basic Research</i> , 2000, 221, 49-53.	1.5	21
94	Measuring Excitonic Coherence in Nanostructures: Time-Resolved Speckle Analysis versus Four-Wave Mixing. <i>Physica Status Solidi A</i> , 2000, 178, 13-20.	1.7	7
95	Room-Temperature Dephasing in InAs Quantum Dots. <i>Physica Status Solidi A</i> , 2000, 178, 337-340.	1.7	1
96	Dephasing and interaction of excitons in CdSe/ZnSe islands. <i>Journal of Crystal Growth</i> , 2000, 214-215, 747-751.	1.5	7
97	Long-time luminescence kinetics of localized excitons and conduction band edge smearing in ZnSe(1-x)Te solid solutions. <i>JETP Letters</i> , 2000, 72, 320-323.	1.4	7
98	Interwell excitons in GaAs/AlGaAs double quantum wells and their collective properties. <i>Journal of Experimental and Theoretical Physics</i> , 2000, 90, 1093-1104.	0.9	51
99	Collective behavior of interwell excitons in GaAs/AlGaAs double quantum wells. <i>JETP Letters</i> , 2000, 71, 117-122.	1.4	19
100	InAlGaAs/AlGaAs quantum wells: line widths, transition energies and segregation. <i>Microelectronic Engineering</i> , 2000, 51-52, 257-264.	2.4	2
101	Magnetophonon resonance in photoluminescence excitation spectra of magnetoexcitons in GaAs/Al <sub>0.3</sub> Ga <sub>0.7</sub> As superlattice. <i>Physical Review B</i> , 2000, 62, 2743-2750.	3.2	4
102	Exciton localization and interface roughness in growth-interrupted GaAs/AlAs quantum wells. <i>Physical Review B</i> , 2000, 61, 10322-10329.	3.2	82
103	Biexcitons or bipolaritons in a semiconductor microcavity. <i>Physical Review B</i> , 2000, 62, R7763-R7766.	3.2	34
104	Phase diagram of a two-dimensional liquid in GaAs/Al <sub>x</sub> Ga <sub>1-x</sub> As biased double quantum wells. <i>Physical Review B</i> , 2000, 61, 8420-8424.	3.2	31
105	Quantum kinetic exciton-LO-phonon interaction in CdSe. <i>Physical Review B</i> , 2000, 61, 1935-1940.	3.2	46
106	Instantaneous Rayleigh scattering from excitons localized in monolayer islands. <i>Physical Review B</i> , 2000, 61, R10555-R10558.	3.2	7
107	Ultrannarrow polaritons in a semiconductor microcavity. <i>Applied Physics Letters</i> , 2000, 76, 3262-3264.	3.3	33
108	Resonant Rayleigh Scattering of Exciton-Polaritons in Multiple Quantum Wells. <i>Physical Review Letters</i> , 2000, 85, 650-653.	7.8	43

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109	Second-harmonic imaging of semiconductor quantum dots. Applied Physics Letters, 2000, 77, 806-808.	3.3	15
110	Direct evidence of reduced dynamic scattering in the lower polariton of a semiconductor microcavity. Physical Review B, 2000, 61, R13377-R13380.	3.2	24
111	Dephasing in the quasi-two-dimensional exciton-biexciton system. Physical Review B, 2000, 61, 1692-1695.	3.2	70
112	Separation of coherent and incoherent nonlinearities in a heterodyne pump-probe experiment. Optics Express, 2000, 7, 107.	3.4	23
113	Spectral hole-burning and carrier-heating dynamics in InGaAs quantum-dot amplifiers. IEEE Journal of Selected Topics in Quantum Electronics, 2000, 6, 544-551.	2.9	161
114	Ultrafast gain dynamics in InAs-InGaAs quantum-dot amplifiers. IEEE Photonics Technology Letters, 2000, 12, 594-596.	2.5	156
115	Time-resolved optical characterization of InAs/InGaAs quantum dots emitting at 1.3 $\mu$ m. Applied Physics Letters, 2000, 76, 3430-3432.	3.3	85
116	Measurement of pulse amplitude and phase distortion in a semiconductor optical amplifier: from pulse compression to breakup. IEEE Photonics Technology Letters, 2000, 12, 1674-1676.	2.5	33
117	Time-resolved four-wave mixing in InAs/InGaAs quantum-dot amplifiers under electrical injection. Applied Physics Letters, 2000, 76, 1380-1382.	3.3	43
118	Transient four-wave mixing in T-shaped GaAs quantum wires. Physical Review B, 1999, 60, 16667-16674.	3.2	27
119	Well-width dependence of exciton-phonon scattering in $\text{In}_x\text{Ga}_{1-x}\text{As}$ /GaAs single quantum wells. Physical Review B, 1999, 59, 2215-2222.	3.2	66
120	Mixed biexcitons in single quantum wells. Physical Review B, 1999, 59, 4584-4587.	3.2	47
121	Binding energy and dephasing of biexcitons in $\text{In}_{0.18}\text{Ga}_{0.82}\text{As}$ /GaAs single quantum wells. Physical Review B, 1999, 60, 4505-4508.	3.2	39
122	Interaction-induced effects in the nonlinear coherent response of quantum-well excitons. Physical Review B, 1999, 60, 4454-4457.	3.2	40
123	Localization-enhanced biexciton binding in semiconductors. Physical Review B, 1999, 59, 15405-15408.	3.2	48
124	Exciton dynamics in $\text{GaAs}/\text{Al}_x\text{Ga}_{1-x}\text{As}$ quantum wells. Physical Review B, 1999, 59, 10255-10260.	3.2	15
125	Excitons, biexcitons, and phonons in ultrathin CdSe/ZnSe quantum structures. Physical Review B, 1999, 60, 8773-8782.	3.2	115
126	Time-Resolved Speckle Analysis: A New Approach to Coherence and Dephasing of Optical Excitations in Solids. Physical Review Letters, 1999, 82, 1040-1043.	7.8	123



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127	Exciton dephasing and biexciton binding in CdSe/ZnSe islands. <i>Physical Review B</i> , 1999, 60, 10640-10643.	3.2	25
128	Measurement and calculation of the critical pulsewidth for gain saturation in semiconductor optical amplifiers. <i>Optics Communications</i> , 1999, 164, 51-55.	2.1	45
129	Heterodyne pump-probe and four-wave mixing in semiconductor optical amplifiers using balanced lock-in detection. <i>Optics Communications</i> , 1999, 169, 317-324.	2.1	66
130	Image Formation in Second-Harmonic Near-Field Microscopy. <i>Physica Status Solidi A</i> , 1999, 175, 331-336.	1.7	5
131	Optical anisotropy in vertically coupled quantum dots. <i>Physical Review B</i> , 1999, 60, 16680-16685.	3.2	80
132	Luminescence spectra and kinetics of disordered solid solutions. <i>Physical Review B</i> , 1999, 59, 12947-12972.	3.2	65
133	Dephasing in InAs/GaAs quantum dots. <i>Physical Review B</i> , 1999, 60, 7784-7787.	3.2	117
134	Optical properties of InAlGaAs quantum wells: Influence of segregation and band bowing. <i>Journal of Applied Physics</i> , 1999, 86, 2584-2589.	2.5	40
135	Charged excitonic complexes in GaAs/Al <sub>0.35</sub> Ga <sub>0.65</sub> As p-i-n double quantum wells. <i>Physical Review B</i> , 1999, 60, 8897-8901.	3.2	22
136	Polarization-resolved imaging with a reflection near-field optical microscope. <i>Journal of the Optical Society of America A: Optics and Image Science, and Vision</i> , 1999, 16, 2649.	1.5	8
137	<title>Ultrafast dynamics of confined and localized excitons in low-dimensional semiconductors</title>. , 1999, , .		0
138	Thermalization of free excitons in ZnSe quantum wells. <i>Journal of Crystal Growth</i> , 1998, 184-185, 795-800.	1.5	19
139	Transient measurements with an ultrafast scanning tunneling microscope. <i>Applied Physics A: Materials Science and Processing</i> , 1998, 66, S23-S26.	2.3	5
140	Direct and spatially indirect excitons in GaAs/AlGaAs superlattices in strong magnetic fields. <i>Physics of the Solid State</i> , 1998, 40, 767-769.	0.6	2
141	Effect of the coherence of free electron-hole pairs on excitonic absorption in GaAs/AlGaAs superlattices. <i>JETP Letters</i> , 1998, 67, 67-72.	1.4	0
142	Interwell radiative recombination in the presence of random potential fluctuations in GaAs/AlGaAs biased double quantum wells. <i>JETP Letters</i> , 1998, 67, 613-620.	1.4	9
143	Localized Biexcitons in Quasi-2D and Quasi-3D Systems. <i>Physica Status Solidi (B): Basic Research</i> , 1998, 206, 111-118.	1.5	17
144	3D versus 1D Quantum Confinement in Coherently Strained CdS/ZnS Quantum Structures. <i>Physica Status Solidi (B): Basic Research</i> , 1998, 206, 501-506.	1.5	5

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145	Sub-wavelength imaging by depolarization in a reflection near-field optical microscope using an uncoated fiber probe. Optics Communications, 1998, 146, 277-284.	2.1	16
146	Enhancement of exchange interaction in ultrathin CdS/ZnS quantum structures. Solid State Communications, 1998, 106, 653-657.	1.9	19
147	Interaction-induced dephasing of excitons in wide ZnSe/ZnMgSe single quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 1998, 2, 82-86.	2.7	3
148	Optimizing the fabrication of aluminum-coated fiber probes and their application to optical near-field lithography. Ultramicroscopy, 1998, 71, 65-71.	1.9	14
149	Dispersion of the second-order nonlinear susceptibility in ZnTe, ZnSe, and ZnS. Physical Review B, 1998, 58, 10494-10501.	3.2	120
150	Direct observation of free-exciton thermalization in quantum-well structures. Physical Review B, 1998, 57, 1390-1393.	3.2	114
151	Direct characterization of ultraviolet-light-induced refractive index structures by scanning near-field optical microscopy. IEEE Photonics Technology Letters, 1998, 10, 848-850.	2.5	5
152	Influence of random potential fluctuations on the interwell radiative recombination in biased double quantum well. Europhysics Letters, 1998, 41, 535-540.	2.0	15
153	Exciton dephasing in ZnSe quantum wires. Physical Review B, 1998, 57, 1797-1800.	3.2	25
154	Femtosecond tunneling response of surface plasmon polaritons. Applied Physics Letters, 1998, 72, 3074-3076.	3.3	13
155	Transient measurements with an ultrafast scanning tunneling microscope on semiconductor surfaces. Applied Physics Letters, 1998, 72, 1644-1646.	3.3	16
156	Interaction and dephasing of center-of-mass quantized excitons in wide ZnSe/Zn <sub>0.94</sub> Mg <sub>0.06</sub> Se quantum wells. Physical Review B, 1998, 57, 1791-1796.	3.2	38
157	Second-harmonic imaging of ferroelectric domain walls. Applied Physics Letters, 1998, 73, 1814-1816.	3.3	77
158	Relaxation of Nonthermal hh and lh Excitons in ZnSe Quantum Wells. Physica Status Solidi (B): Basic Research, 1998, 206, 103-109.	1.5	0
159	Binding-energy distribution and dephasing of localized biexcitons. Physical Review B, 1997, 55, R7383-R7386.	3.2	75
160	Spatio-temporal imaging of voltage pulses with an ultrafast scanning tunneling microscope. Applied Physics Letters, 1997, 70, 2762-2764.	3.3	13
161	Binding of biexcitons in GaAs/Al <sub>x</sub> Ga <sub>1-x</sub> As superlattices. Physical Review B, 1997, 55, 5284-5289.	3.2	16
162	Measuring voltage transients with an ultrafast scanning tunneling microscope. Applied Physics Letters, 1997, 70, 2625-2627.	3.3	18

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163	Coherent dynamics of interwell excitons in GaAs/Al <sub>x</sub> Ga <sub>1-x</sub> As superlattices. <i>Physical Review B</i> , 1997, 55, 7743-7748.	3.2	3
164	Coherent optical nonlinearities and phase relaxation of quasi-three-dimensional and quasi-two-dimensional excitons in ZnS <sub>x</sub> Se <sub>1-x</sub> /ZnSe structures. <i>Physical Review B</i> , 1997, 56, 12581-12588.	3.2	30
165	Continuum contribution to excitonic four-wave mixing due to interaction-induced nonlinearities: A numerical study. <i>Physical Review B</i> , 1997, 55, 2456-2465.	3.2	40
166	Femtosecond differential transmission measurements on low temperature GaAs metal-semiconductor-metal structures. <i>Applied Physics Letters</i> , 1997, 70, 72-74.	3.3	18
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